

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	277442	sti or isolation or trench	USPAT	OR	ON	2008/01/12 00:23
L2	1046501	stress\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:23
L3	42050	L1 and L2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:23
L4	38721	L3 and @ad<"20040415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:27
L5	19878	L4 and (transistor or gate or electrode or mos or mosfet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:25
L6	14814	L5 and current	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:23
L7	1951298	semiconductor or (semi adj1 conductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:23
L8	8651	L6 and L7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:23

EAST Search History

L9	5806320	channel or source or drain or "s/d"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:23
L10	7636	L8 and L9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:23
L11	28282	L9 with L2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:23
L12	943	L10 and L11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:24
L13	91537	9 same 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:25
L14	3887632	(transistor or gate or electrode or mos or mosfet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:25
L15	3120	14 and 13 and 7 and 1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:26
L16	2602	15 and @ad<"20040415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/12 00:27